

New Beam Test Results of 3D Pixel Detectors Constructed With Poly-Crystalline CVD Diamond

29th International Symposium on Lepton Photon Interactions at High Energies

Michael Reichmann

8 August 2019

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Section 1

Motivation

- ullet innermost tracking layers o highest radiation damage $\mathcal{O}\left(\mathsf{GHz}/\mathsf{cm}^2\right)$
- \bullet current detectors is designed to survive $\sim 12 \, \text{month}$ in High-Luminosity LHC
- → R&D for more radiation tolerant detector designs and/or materials

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- → R&D for more radiation tolerant detector designs and/or materials

Diamond as Detector Material:

- properties
 - radiation tolerant
 - ▶ isolating material
 - ▶ high charge carrier mobility
 - ► smaller signal than in silicon with same thickness (large bandgap)
 - \blacktriangleright after $1\cdot 10^{16}\,\text{n/cm}^2$ the mean drift path in diamond larger than in silicon

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Work of RD42:

- investigate signals and radiation tolerance in various detector designs:
 - ightharpoonup Pad Detectors ightarrow whole diamond as single cell readout
 - ▶ Pixel Detectors → diamond sensor on pixel readout chip
 - ▶ 3D Pixel Detectors → 3D diamond detector on pixel readout chip

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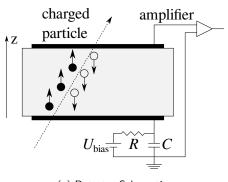
Work of RD42:

- investigate signals and radiation tolerance in various detector designs:
 - ► Pad Detectors
 - ► Pixel Detectors
 - ▶ 3D Pixel Detectors → this talk

Section 2

3D Diamond Detector

Diamond as Particle Detector



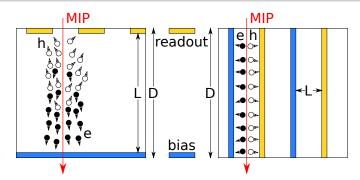
(a) Detector Schematics



(b) 15 cm ø pCVD Diamond Wafer

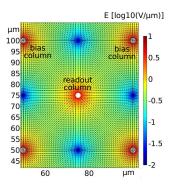
- detectors function as ionisation chambers
- metallisation on both sides
- poly-crystals produced in large wafers

Working Principle



- after large radiation fluence all detectors become trap limited
- 3D = bias and readout electrode inside detector material
- ullet same thickness D o same amount of induced charge o shorter drift distance L
- increase collected charge in detectors with limited mean drift path (Schubweg)
- introduce low field regions

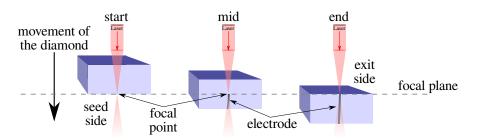
Electric Field Simulation



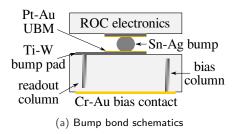
- simulation with 30 V bias voltage and periodic boundary conditions
- \bullet electric field ${\sim}1\,V/\mu m$ over a large area in the cell
- low field region in between the electrodes

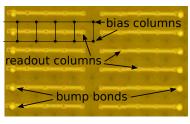
Laser drilling

- "drilling" columns using 800 nm fs-LASER (Oxford)
- convert diamond into resistive mixture of carbon phases (i.a. DLC, graphite, ...)
- usage of Spatial Light Modulation (SLM) to correct for vertical aberration
- initial column yield $\sim 90 \% \rightarrow \text{now} \ge 99 \%$
- ullet initial column diameter 6 \sim 10 μ m \to now 2.6 μ m



Bump Bonding

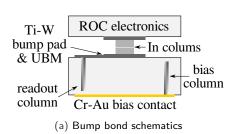


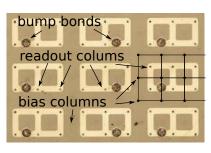


(b) 5×1 bump pads

- connection to bias and readout with surface metallisation
- ganging of cells to match pixel pitch of readout-chip (ROC)
- \bullet small gap (\sim 15 μ m) to the surface

Bump Bonding





(b) 3×2 bump pads

- connection to bias and readout with surface metallisation
- ganging of cells to match pixel pitch of readout-chip (ROC)
- \bullet small gap (\sim 15 μ m) to the surface

Progress in Diamond Detectors

3D Detectors - History in Diamonds:

- proved that 3D works in pCVD diamond
- ullet scale up the number of columns per detector: $\mathcal{O}\left(100
 ight)
 ightarrow \mathcal{O}\left(1000
 ight) \left(\mathsf{x40}
 ight)$
- \bullet reducing the cell size: $150\,\mu m \times 150\,\mu m \to 50\,\mu m \times 50\,\mu m \to 25\,\mu m \times 25\,\mu m$ (soon)
- ullet reducing the diameter of the columns: $6\sim10\,\mu\text{m}
 ightarrow2.6\,\mu\text{m}
 ightarrow1\sim2\,\mu\text{m}$ (soon)
- ullet \rightarrow increasing column yield: \sim 90 % \rightarrow \geq 99.8 %
- recently tested first irradiated 50 $\mu m \times 50 \, \mu m$ 3D detector $(3.5 \cdot 10^{15} \, n/cm^2)$

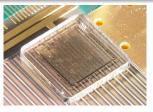
3D Pixel Detectors:

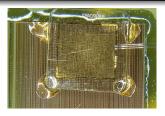
- visible improvements with each step reducing the cell size
- all worked as expected (to first order)

Section 3

Results

Detectors



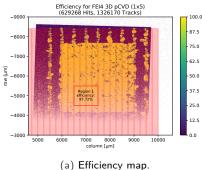


(a) B5

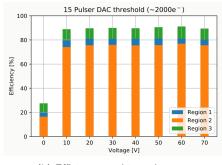
(b) B6

	B5	B6
readout chip (ROC)	FE-I4B	PSI46digv2.1respin
pixel pitch	$250\mu m imes 50\mu m$	$150\mu m imes 100\mu m$
3D cell size	$50\mu\mathrm{m} imes50\mu\mathrm{m}$	$50\mu m imes 50\mu m$
ganging	5 × 1	3 × 2
size	4.90 mm × 4.94 mm	$4.85\text{mm}\times4.90\text{mm}$
thickness	510 μm	500 µm
50 pixels $ imes$ 50 pixels	53 × 67	67×53
3D columns	7223	7223
column diameter	2.6 µm	2.6 µm
active area	$3.2\mathrm{mm} imes 3.5\mathrm{mm}$	$3.45\text{mm}\times3.19\text{mm}$
bump bonding	tin silver (IFAE)	indium (Princeton)

II6-B5 - Efficiencies @ CERN



(a) Efficiency map.



(b) Efficiency vs. bias voltage

- spatial resolution of $\sim 3 \, \mu m$
- ullet threshold of the chip: $\sim\!1000\,\mathrm{e}$
- efficiency in red fiducial area 97.7 %
- inefficiencies most likely due to bump bonding issues

Time Over Threshold

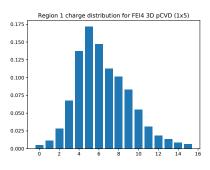
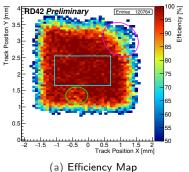


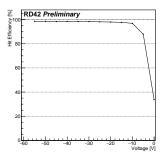
Figure: Time over threshold

- 5 tot $\approx 11000 \, \mathrm{e}$
- ullet MPV of the ToT distribution: $5
 ightarrow 11\,000\,e$
- roughly 80 % the induced charge was collected

II6-B6 - Efficiencies @ PSI



(a) Linciency Mar



(b) Efficiency vs. voltage.

- spatial resolution of $\mathcal{O}(100 \, \mu \text{m})$
- ullet magenta area o bump bonding problems, green area o void in the diamond
- \bullet efficiency in blue box: 99.2 % (\rightarrow 0.4 % due to columns)
- already fully efficient at 30 V
- ROC stopped working after this beam test

Efficiencies @ CERN

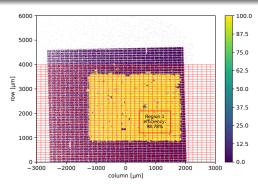


Figure: Efficiency at threshold of \sim 3500 e

- high resolution measurement at CERN
- find non-working/non-connected cells
- sensor twice re-bump-bonded with the same indium (no reprocessing)
 - ▶ no removal of old bumps, no change of surface metallisation
- similar efficiency: 99.1 %

Pulse Height @ CERN

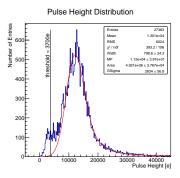


Figure: Pulse height distribution.

- threshold of the chip: \sim 3700 e
- Langau MPV: 11000 e
- ullet pulse height very similar to $5 \, \text{r} \times 1 \, \text{result}$ at CERN
- ullet beam particles at CERN have less energy loss o lower MPV
- also distribution below threshold

Section 4

Conclusion

M. Reichmann (ETH zürich)

Conclusion

- strongly improved fabrication of 3D diamonds
 - ▶ 40 times more cells
 - ► smaller cell size down to 50 μm × 50 μm
 - ► thinner columns down to 2 μm
- 3D Detectors work well in pCVD diamond
- 99.2 % efficiency in 3 × 2 ganged device
 - ▶ inefficiencies due to the columns itself
- 97.7 % efficiency in 5×1 ganged device
 - most likely bump bonding issues
- ullet consistent charge measurements for all devices: $\sim\!11\,000\,\mathrm{e}$ @ CERN SPS
- nearly full charge collection

M. Reichmann (TH zürich)

Section 5

Outlook

Outlook

- \bullet analyse $3.5 \cdot 10^{15} \, n/cm^2$ irradiated $50 \, \mu m \times 50 \, \mu m$ detectors
- \bullet test both $50\,\mu\text{m}\times50\,\mu\text{m}$ and $25\,\mu\text{m}\times25\,\mu\text{m}$ pixel detectors
- \bullet reduce column diameter to $1\sim 2\,\mu m$
- build pixel device on newest RD53 chip ($50 \, \mu m \times 50 \, \mu m$ pixel pitch)
- continue scale up by 10x

